

**Amendments to the Claims:**

This listing of the claims will replace all prior versions and listings of claims in this application.

**Listing of Claims:**

What is claimed is:

**Claim 1 (Currently Amended).** A method of stripping an integrated circuit (IC) structure having a photoresist material, ~~and~~ an organosilicate glass (OSG) material and a via etched into said IC structure, comprising:

feeding a nitrous oxide (N<sub>2</sub>O) gas into a reactor;

generating a plasma is in said reactor; stripping said photoresist;

generating an organic plug that occupies said via, and stripping said

organic plug with said N<sub>2</sub>O gas; and

generating a high selectivity between said photoresist and said OSG.

**Claim 2 (Original).** The method of claim 1 wherein said photoresist is an organic photoresist.

**Claim 3 (Original).** The method of claim 2 wherein said stripping said photoresist is one of a plurality of steps performed during a dual damascene process.

**Claim 4 (Original).** The method of claim 3 wherein said stripping of said photoresist is performed in the same reactor used for etching said OSG material.

~~**Claim 5 (Canceled).** The method of claim 1 further comprising, providing a via etched into said IC structure; generating an organic plug that occupies said via; and stripping said organic plug with said N<sub>2</sub>O gas.~~

**Claim 6 (Currently Amended).** A method of stripping an integrated circuit (IC) structure including a first photoresist layer, a second intermediate layer, and a third organosilicate glass (OSG) layer, comprising:

- feeding a nitrous oxide (N<sub>2</sub>O) gas into a reactor;
- generating a plasma in said reactor;
- stripping said photoresist with said plasma;
- generating a high selectivity between said first photoresist layer and said second intermediate layer;
- stripping said second intermediate layer with said plasma; and
- generating a high selectivity between said first photoresist layer and said third OSG layer.

**Claim 7 (Original).** The method of claim 6 wherein said photoresist is an organic photoresist.

**Claim 8 (Original).** The method of claim 6 wherein said stripping of said photoresist is performed in the same reactor used for etching said OSG layer.

**Claim 9 (Original).** The method of claim 6 wherein said stripping said photoresist is one of a plurality of steps performed during a dual damascene process.

**Claim 10 (Original).** The method of claim 6 wherein said second intermediate layer is a cap layer.

**Claim 11 (Original).** The method of claim 10 wherein said cap layer is a selected from a group consisting of Silicon Dioxide ( $\text{SiO}_2$ ) and Silicon Oxynitride ( $\text{SiON}$ ).

**Claim 12 (Original).** The method of claim 6 wherein said second intermediate layer is a hardmask layer.

**Claim 13 (Original).** The method of claim 12 wherein said hardmask layer is selected from a group consisting of Silicon Nitride ( $\text{Si}_3\text{N}_4$ ), Tantalum Nitride ( $\text{TaN}$ ), Titanium Nitride ( $\text{TiN}$ ), and Silicon Carbide ( $\text{SiC}$ ).

**Claim 14 (Currently Amended).** A method of performing a via first etch with an IC structure including a first photoresist layer, a second cap layer, and a third organosilicate glass (OSG) layer, comprising:

~~firstly~~, etching a via into said second cap layer and said third OSG layer;  
and

~~secondly~~, stripping said first photoresist layer with a nitrous oxide (N<sub>2</sub>O) gas;

generating an organic plug within said via; and

stripping said organic plug with said N<sub>2</sub>O gas.

**Claim 15 (Currently Amended).** The method of claim 14 wherein said further comprising, ~~thirdly~~, generating an organic plug within with said via that occupies part of said third OSG layer.

**Claim 16 (Currently Amended).** The method of claim 15 further comprising, ~~fourthly~~, etching a trench into said second cap layer and said third OSG layer and applying another first photoresist layer.

**Claim 17 (Currently Amended).** The method of claim 15 further comprising, ~~fifthly~~, stripping said other first photoresist layer and said organic plug with said N<sub>2</sub>O gas.

**Claim 18 (Original).** The method of claim 17 wherein said photoresist is an organic photoresist.

**Claim 19 (Original).** The method of 18 wherein said stripping said photoresist is one of a plurality of steps performed during a dual damascene process.

**Claim 20 (Currently Amended).** A method of performing a trench first etch with an IC structure including a first photoresist layer, a second hardmask layer, and a third organosilicate glass (OSG) layer, comprising:

firstly, etching a trench into said second hardmask layer; and  
secondly, stripping said first photoresist layer with a nitrous oxide (N<sub>2</sub>O) gas;  
applying another first photoresist layer for performing a via etch;  
etching a via into said second hardmask layer, and said third OSG layer;  
stripping said other first photoresist layer with said N<sub>2</sub>O gas;  
generating an organic plug within said via, and  
using said N<sub>2</sub>O gas to strip said organic plug.

**Claim 21 (Canceled).** ~~The method of claim 20 further comprising, thirdly,~~  
~~applying another first photoresist layer for performing a via etch.~~

**Claim 22 (Canceled).** ~~The method of claim 21 further comprising, fourthly,~~  
~~etching a via into said second hardmask layer, and said third OSG layer.~~

**Claim 23 (Canceled).** ~~The method of claim 22 further comprising, fifthly, stripping said other first photoresist layer with said N<sub>2</sub>O gas.~~

**Claim 24 (Currently Amended).** The method of claim 20 ~~23~~ wherein said further comprising, ~~sixthly, generating an organic plug within said via that~~ occupies part of said third OSG layer.

**Claim 25 (Currently Amended).** The method of claim 24 further comprising, ~~seventhly, etching a second~~ said trench into said third OSG layer.

**Claim 26 (Currently Amended).** The method of claim 25 further comprising, ~~eighthly, using said N<sub>2</sub>O gas to strip said organic plug.~~